Dual 4-Input NAND Gate

High-Performance Silicon-Gate CMOS

Features

- Outputs Source/Sink 24 mA
- 'ACT20 Has TTL Compatible Inputs
- These are Pb–Free Devices

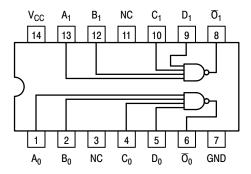


Figure 1. Pinout: 14-Lead Packages (Top View)

PIN ASSIGNMENT

PIN	FUNCTION
A _n , B _n , C _n , D _n	Inputs
Ōn	Outputs



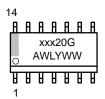
ON Semiconductor®

www.onsemi.com





SOIC-14 D SUFFIX CASE 751A



xxx = AC or ACT

A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
VI	DC Input Voltage	$-0.5 \le V_{I} \le V_{CC} + 0.5$	V
Vo	DC Output Voltage (Note 1)	$-0.5 \le V_{O} \le V_{CC} + 0.5$	V
I _{IK}	DC Input Diode Current	±20	mA
I _{OK}	DC Output Diode Current	±50	mA
I _O	DC Output Sink/Source Current	±50	mA
I _{CC}	DC Supply Current per Output Pin	±50	mA
I _{GND}	DC Ground Current per Output Pin	±50	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
TL	Lead temperature, 1 mm from Case for 10 Seconds	260	°C
TJ	Junction temperature under Bias	+150	°C
θ_{JA}	Thermal Resistance (Note 2)	125	°C/W
P _D	Power Dissipation in Still Air at 85°C	125	mW
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 30% – 35%	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 3) Machine Model (Note 4) Charged Device Model (Note 5)	> 2000 > 200 > 1000	V
I _{Latch-Up}	Latch-Up Performance Above V _{CC} and Below GND at 85°C (Note 6)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. I_O absolute maximum rating must be observed.
- The package thermal impedance is calculated in accordance with JESD51-7.
- 3. Tested to EIA/JESD22-A114-A.
- 4. Tested to EIA/JESD22-A115-A.
- 5. Tested to JESD22-C101-A.
- 6. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Тур	Min	Unit
V	Supply Voltage		2.0	5.0	6.0	
VCC	V _{CC} Supply Voltage	'ACT	4.5	5.0	5.5	V
VREG	DC Regulated Power Voltage (Ref. to GND)		0	-	V _{CC}	V
		V _{CC} @ 3.0 V	-	150	-	
t _r , t _f	Input Rise and Fall Time (Note 1) 'AC Devices except Schmitt Inputs	V _{CC} @ 4.5 V	-	40	-	ns/V
		V _{CC} @ 5.5 V	_	25	-	
	Input Rise and Fall Time (Note 2)	V _{CC} @ 4.5 V	_	10	-	ns/V
t _r , t _f	'ACT Devices except Schmitt Inputs	V _{CC} @ 5.5 V	_	8.0	-	TIS/V
TJ	Junction Temperature (PDIP)		_	-	140	°C
T _A	Operating Ambient Temperature Range			25	85	°C
I _{OH}	Output Current – HIGH		-	-	-24	mA
I _{OL}	Output Current – LOW		-	-	24	mA

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

1. V_{in} from 30% to 70% V_{CC}; see individual Data Sheets for devices that differ from the typical input rise and fall times.

2. V_{in} from 0.8 V to 2.0 V; see individual Data Sheets for devices that differ from the typical input rise and fall times.

DC CHARACTERISTICS

			74	AC	74AC		
Symbol	Parameter	V _{CC} (V)	T _A = +25°C		T _A = -40°C to +85°C	Unit	Conditions
			Тур	Guar	anteed Limits		
V_{IH}	Minimum High Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	2.1 3.15 3.85	2.1 3.15 3.85	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V_{IL}	Maximum Low Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	0.9 1.35 1.65	0.9 1.35 1.65	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{OH}	Minimum Low Level Output Voltage	3.0 4.5 5.5	2.99 4.49 5.49	2.9 4.4 5.4	2.9 4.4 5.4	V	I _{OUT} = - 50 μA
		3.0 4.5 5.5		2.56 3.86 4.86	2.46 3.76 4.76	V	* V _{IN} = V _{IL} or V _{IH} $-$ 12 mA I_{OH} $-$ 24 mA $-$ 24 mA
V _{OL}	Maximum Low Level Output Voltage	3.0 4.5 5.5	0.002 0.001 0.001	0.1 0.1 0.1	0.1 0.1 0.1	V	Ι _{ΟUT} = 50 μΑ
		3.0 4.5 5.5	- - -	0.36 0.36 0.36	0.44 0.44 0.44	V	* V _{IN} = V _{IL} or V _{IH} 12 mA I OL 24 mA 24 mA
I _{IN}	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μΑ	$V_I = V_{CC}$, GND
I _{OLD}	†Minimum Dynamic	5.5	-	-	75	mA	V _{OLD} = 1.65 V Max
I _{OHD}	Output Current	5.5	-	_	- 75	mA	V _{OHD} = 3.85 V Min
I _{CC}	Maximum Quiescent Supply Current	5.5	_	4.0	40	μΑ	$V_{IN} = V_{CC}$ or GND

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

*All outputs loaded; thresholds on input associated with output under test.

NOTE: I_{IN} and I_{CC} @ 3.0 V are guaranteed to be less than or equal to the respective limit @ 5.5 V.

AC CHARACTERISTICS

			74AC			74AC		
Symbol	Parameter	V _{CC} * (V)		₄ = +25° _L = 50 p		T _A = - to +8 C _L = 8	35°C	Unit
			Min	Тур	Max	Min	Max	
t _{PLH}	Propagation Delay	3.3 5.0	2.0 1.5	6.0 5.0	8.5 7.0	1.5 1.0	10.0 8.0	ns
t _{PHL}	Propagation Delay	3.3 5.0	1.5 1.5	5.0 4.0	7.0 6.0	1.0 1.0	9.0 7.0	ns

^{*}Voltage Range 3.3 V is 3.3 V ± 0.3 V. Voltage Range 5.0 V is 5.0 V ±0.5 V.

[†]Maximum test duration 2.0 ms, one output loaded at a time.

DC CHARACTERISTICS

			74 <i>A</i>	CT	74ACT		
Symbol	Parameter	V _{CC} (V)	T _A = +25°C		T _A = -40°C to +85°C	Unit	Conditions
			Тур	Guar	anteed Limits		
V _{IH}	Minimum High Level Input Voltage	4.5 5.5	1.5 1.5	2.0 2.0	2.0 2.0	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{IL}	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{OH}	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4	V	I _{OUT} = - 50 μA
		4.5 5.5	- -	3.86 4.86	3.76 4.76	V	$^*V_{IN} = V_{IL} \text{ or } V_{IH}$ -24 mA I_{OH} -24 mA
V _{OL}	Maximum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1	V	I _{OUT} = 50 μA
		4.5 5.5	- -	0.36 0.36	0.44 0.44	V	$^*V_{IN} = V_{IL} \text{ or } V_{IH}$ $^24 \text{ mA}$ 1OH $^24 \text{ mA}$
I _{IN}	Maximum Input Leakage Current	5.5	_	±0.1	±1.0	μΑ	$V_I = V_{CC}$, GND
ΔI_{CCT}	Additional Max. I _{CC} /Input	5.5	0.6	_	1.5	mA	$V_{I} = V_{CC} - 2.1 \text{ V}$
I _{OLD}	†Minimum Dynamic	5.5	-	_	75	mA	V _{OLD} = 1.65 V Max
I _{OHD}	Output Current	5.5	-	_	-75	mA	V _{OHD} = 3.85 V Min
Icc	Maximum Quiescent Supply Current	5.5	_	4.0	40	μΑ	$V_{IN} = V_{CC}$ or GND

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

*All outputs loaded; thresholds on input associated with output under test.

*Maximum test duration 2.0 ms. one output loaded at a first.

AC CHARACTERISTICS

			74ACT			74ACT		Unit
Symbol	Parameter	V _{CC} * (V)	T _A = +25°C C _L = 50 pF		T _A = -40°C to +85°C C _L = 50 pF			
			Min	Тур	Max	Min	Max	
t _{PLH}	Propagation Delay	5.0	2.0	6.5	9.0	1.5	10.5	ns
t _{PHL}	Propagation Delay	5.0	2.0	5.5	9.0	1.5	10.5	ns

^{*}Voltage Range 5.0 V is 5.0 V ± 0.5 V.

CAPACITANCE

Symbol	Parameter	Value Typ	Unit	Test Conditions
C _{IN}	Input Capacitance	4.5	pF	V _{CC} = 5.0 V
C _{PD}	Power Dissipation Capacitance	40	pF	V _{CC} = 5.0 V

[†]Maximum test duration 2.0 ms, one output loaded at a time.

ORDERING INFORMATION

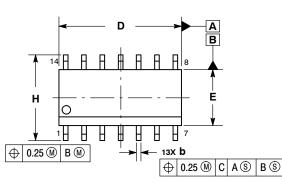
Device	Package	Shipping †
MC74AC20DG	SOIC-14 (Pb-Free)	55 Units/Rail
MC74AC20DR2G	SOIC-14 (Pb-Free)	2500/Tape & Reel
MC74ACT20DG	SOIC-14 (Pb-Free)	55 Units/Rail
MC74ACT20DR2G	SOIC-14 (Pb-Free)	2500/Tape & Reel

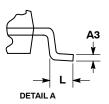


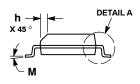
△ 0.10

SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016







SIDE.

AIL A

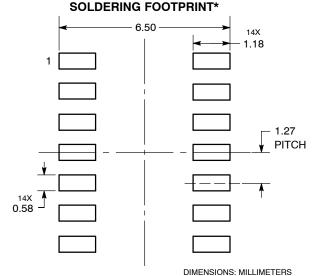
| MILLIMETER:
| DIM | MIN | MAX
| A | 1.35 | 1.75

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.35	1.75	0.054	0.068	
A1	0.10	0.25	0.004	0.010	
АЗ	0.19	0.25	0.008	0.010	
b	0.35	0.49	0.014	0.019	
D	8.55	8.75	0.337	0.344	
Е	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050	BSC	
H	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.019	
L	0.40	1.25	0.016	0.049	
М	0 °	7°	0 °	7°	

5. MAXIMUM MOLD PROTRUSION 0.15 PER

NOTES:
1. DIMENSIONING AND TOLERANCING PER

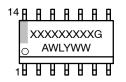
ASME Y14.5M, 1994.
CONTROLLING DIMENSION: MILLIMETERS.
DIMENSION b DOES NOT INCLUDE DAMBAR
PROTRUSION. ALLOWABLE PROTRUSION
SHALL BE 0.13 TOTAL IN EXCESS OF AT
MAXIMUM MATERIAL CONDITION.
DIMENSIONS D AND E DO NOT INCLUDE
MOLD PROTRUSIONS.



C SEATING PLANE

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Repo Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOIC-14 NB		PAGE 1 OF 2		

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

SOIC-14 CASE 751A-03 ISSUE L

DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-14 NB		PAGE 2 OF 2

ON Semiconductor and IN are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800–282–9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative